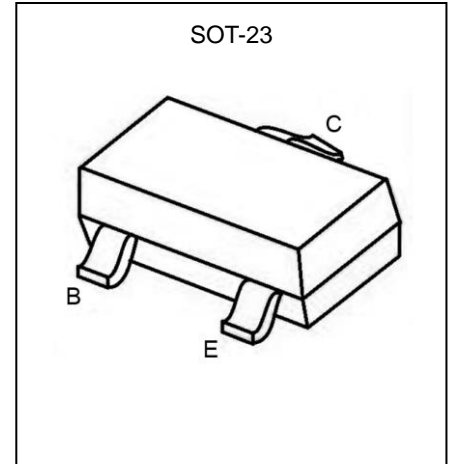




**BC817 Transistor(NPN)**

**Feature**

- For general AF applications
- High collector current
- High current gain
- Complementary type: BC807(PNP)



**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

| Parameter                     | Symbol           | Value     | Unit |
|-------------------------------|------------------|-----------|------|
| Collector-Base Voltage        | V <sub>CBO</sub> | 50        | V    |
| Collector-Emitter Voltage     | V <sub>CEO</sub> | 45        | V    |
| Emitter-Base Voltage          | V <sub>EBO</sub> | 5         | V    |
| Collector Current -Continuous | I <sub>c</sub>   | 0.5       | A    |
| Power Dissipation             | P <sub>d</sub>   | 0.3       | W    |
| Junction Temperature          | T <sub>J</sub>   | 150       | °C   |
| Storage Temperature           | T <sub>STG</sub> | -55~ +150 | °C   |

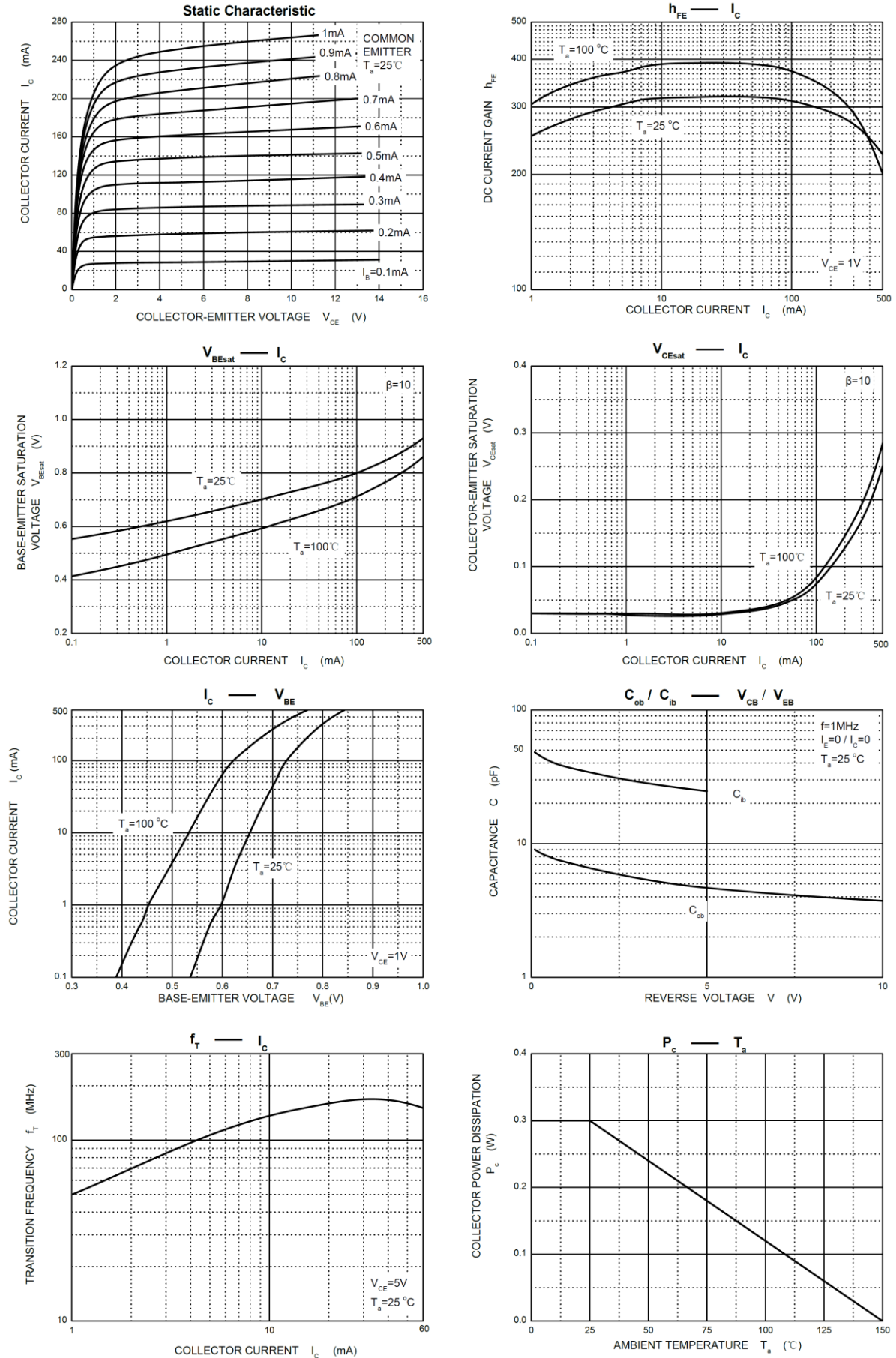
**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

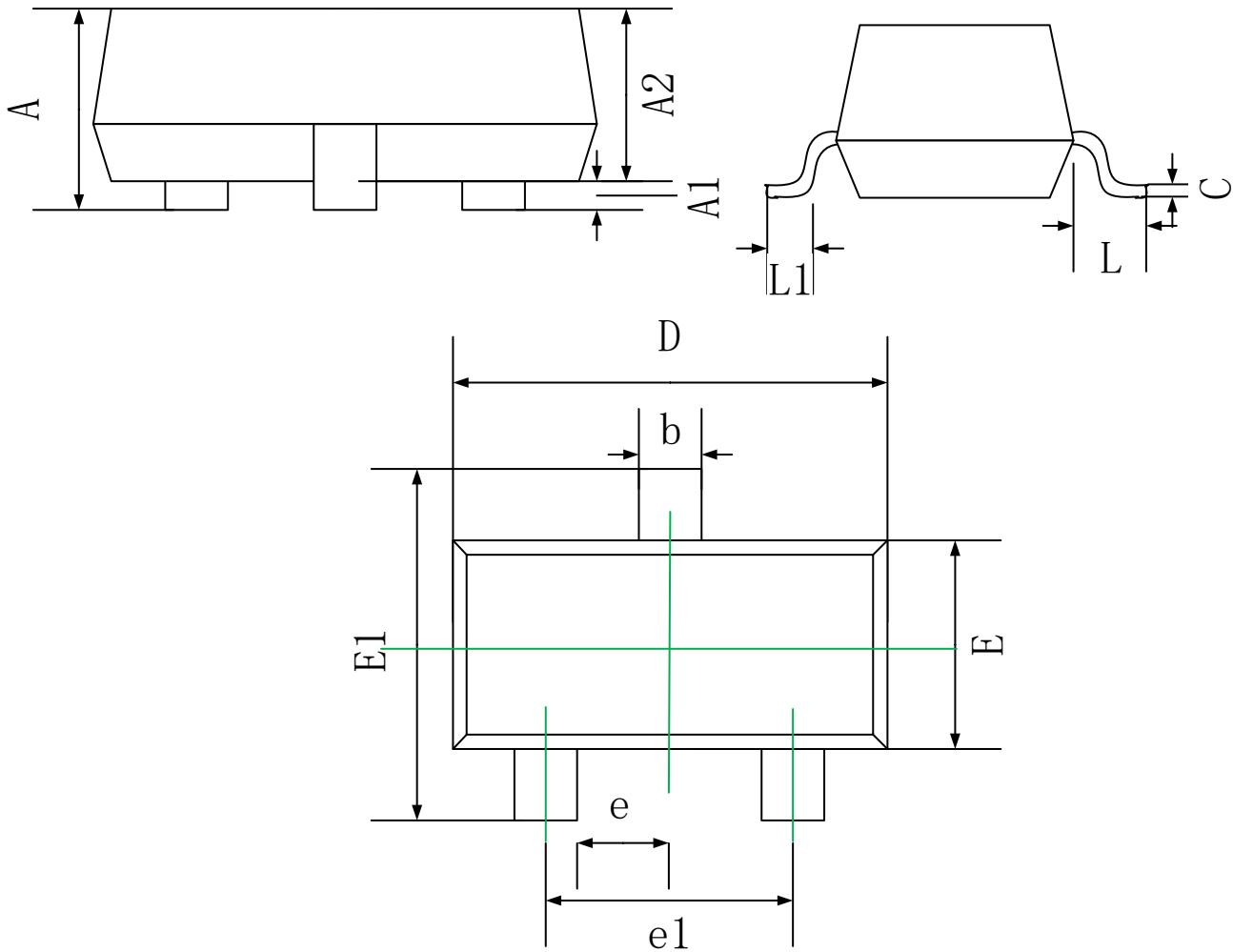
| Parameter                            | Symbol               | Test Condition                                       | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|-----|------|
| Collector-base breakdown voltage     | V <sub>(BR)CBO</sub> | I <sub>c</sub> =10μA , I <sub>E</sub> =0             | 50  |     |     | V    |
| Collector-emitter breakdown voltage  | V <sub>(BR)CEO</sub> | I <sub>c</sub> =10mA , I <sub>B</sub> =0             | 45  |     |     | V    |
| Emitter-base breakdown voltage       | V <sub>(BR)EBO</sub> | I <sub>E</sub> =1μA, I <sub>c</sub> =0               | 5   |     |     | V    |
| Collector cut-off current            | I <sub>CBO</sub>     | V <sub>CB</sub> =45V, I <sub>E</sub> =0              |     |     | 0.1 | μA   |
| Emitter cut-off current              | I <sub>EBO</sub>     | V <sub>EB</sub> =4V, I <sub>c</sub> =0               |     |     | 0.1 | μA   |
| DC current gain                      | h <sub>FE1</sub>     | V <sub>CE</sub> =1V, I <sub>c</sub> =100mA           | 100 |     | 600 |      |
|                                      | h <sub>FE2</sub>     | V <sub>CE</sub> =1V, I <sub>c</sub> =500mA           | 40  |     |     |      |
| Collector-emitter saturation voltage | V <sub>CE(sat)</sub> | I <sub>c</sub> =500mA, I <sub>B</sub> =50mA          |     |     | 0.7 | V    |
| Base-emitter saturation voltage      | V <sub>BE(sat)</sub> | I <sub>c</sub> =500mA, I <sub>B</sub> =50mA          |     |     | 1.1 | V    |
| Transition frequency                 | f <sub>T</sub>       | V <sub>CE</sub> =5V, I <sub>c</sub> =10mA, f =100MHz | 100 |     |     | MHZ  |
| Input capacitance                    | C <sub>OB</sub>      | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz      |     | 10  |     | pF   |

**Classification of h<sub>FE1</sub>**

| Rank    | BC817-16 | BC817-25 | BC817-40 |
|---------|----------|----------|----------|
| Range   | 100~250  | 160~400  | 250~600  |
| Marking | 6A       | 6B       | 6C       |

**Typical Characteristics**



**SOT-23 Package Information**


| Symbol | Dimensions In Millimeters |      |
|--------|---------------------------|------|
|        | Min.                      | Max. |
| A      | 0.90                      | 1.15 |
| A1     | 0.00                      | 0.10 |
| A2     | 0.90                      | 1.05 |
| b      | 0.30                      | 0.50 |
| c      | 0.08                      | 0.15 |
| D      | 2.80                      | 3.00 |
| E      | 1.20                      | 1.40 |
| E1     | 2.25                      | 2.55 |
| e      | 0.95 REF.                 |      |
| e1     | 1.80                      | 2.00 |
| L      | 0.55 REF.                 |      |
| L1     | 0.30                      | 0.50 |

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)